

## Supplementary Information

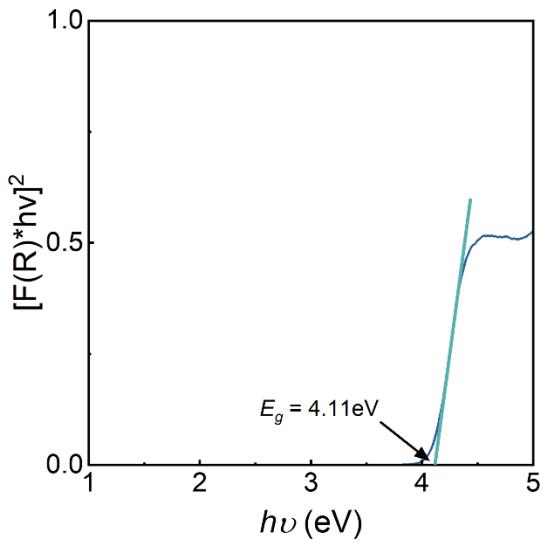
**Efficient near-infrared luminescence in garnet**

### **Na<sub>2</sub>CaTi<sub>2</sub>Ge<sub>3</sub>O<sub>12</sub>:Cr<sup>3+</sup> for light-emitting-diodes applications**

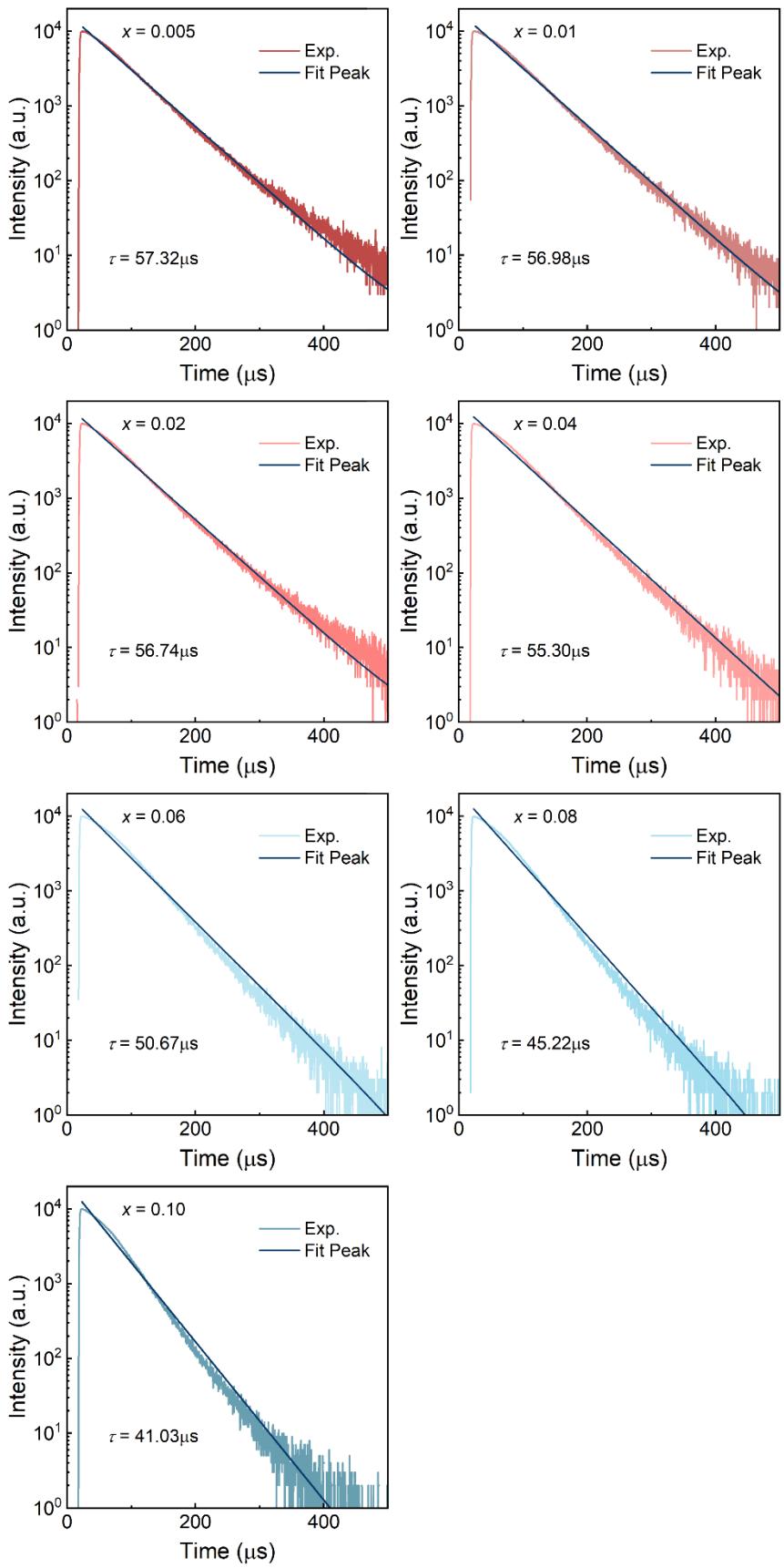
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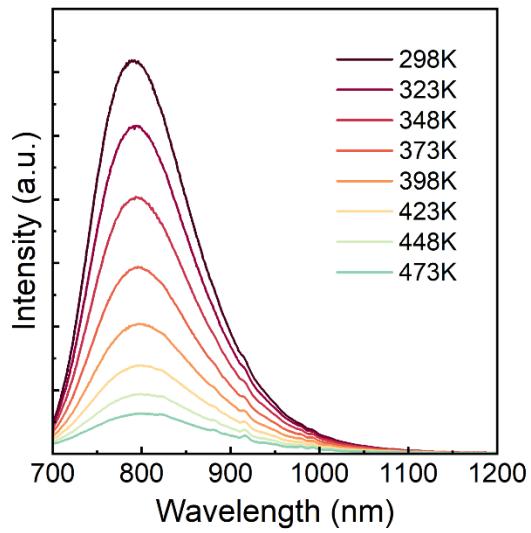
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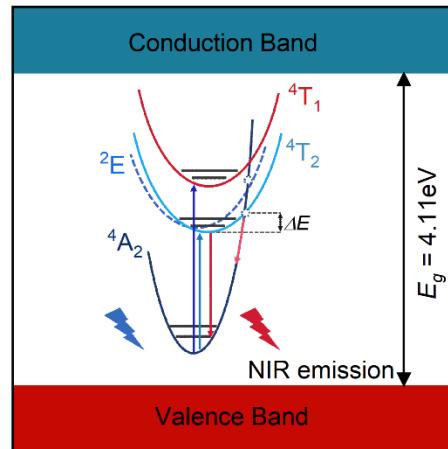
**Fig. S1.** The optical band gap of  $\text{Na}_2\text{CaTi}_2\text{Ge}_3\text{O}_{12}$  sample estimated based on Kubelka–Munk function.



**Fig. S2.** Decay curves of  $\text{Na}_2\text{CaTi}_{2-x}\text{Ge}_3\text{O}_{12}:x\text{Cr}^{3+}$  ( $x = 0.005\text{--}0.10$ ) fitted by single exponential function.



**Fig. S3.** The temperature-dependent emission spectra of  $\text{Na}_2\text{CaTi}_{1.94}\text{Ge}_3\text{O}_{12}:0.06\text{Cr}^{3+}$  sample in temperature range of 298 to 473 K under 465 nm excitation.



**Fig. S4.** Configuration coordinate diagram for  $\text{Cr}^{3+}$  ion luminescence.

**Table S1.** The Refined Atomic Positions of Na<sub>2</sub>CaTi<sub>2</sub>Ge<sub>3</sub>O<sub>12</sub>.

Atom	Wyck. position	Occ.	x	y	z	U <sub>iso</sub>
Na (1)	24c	0.66667	0.125	0	0.25	0.01298
Ca (1)	24c	0.33333	0.125	0	0.25	0.01298
Ti (1)	16a	1	0	0	0	0.01545
Ge (1)	24d	1	0.375	0	0.25	0.01415
O (1)	96h	1	0.098690	0.204770	0.288250	0.01505

**Table S2.** The Refined Atomic Positions of Na<sub>2</sub>CaTi<sub>1.94</sub>Cr<sub>0.06</sub>Ge<sub>3</sub>O<sub>12</sub>.

Atom	Wyck. position	Occ.	x	y	z	U <sub>iso</sub>
Na (1)	24c	0.66667	0.125	0	0.25	0.01257
Ca (1)	24c	0.33333	0.125	0	0.25	0.01257
Ti (1)	16a	0.97	0	0	0	0.01504
Cr (1)	16a	0.03	0	0	0	0.01504
Ge (1)	24d	1	0.375	0	0.25	0.01374
O (1)	96h	1	0.098690	0.204770	0.288250	0.01464

**Table S3.** Input and Output Parameters of Fabricated Device.

Driving currents (mA)	Input power (mW)	NIR Output Power (mW)	Conversion Efficiency
25	65.5	4.852416504	7.41%
50	135	9.541780358	7.07%
75	207	14.07706514	6.80%
100	281	18.23501866	6.49%
125	357.5	21.797598	6.10%
150	435	24.55317315	5.64%
175	514.5	28.42484603	5.52%
200	594	31.09315895	5.23%
225	675	32.94756445	4.88%

250	757.5	36.17725033	4.78%
275	841.5	37.33464158	4.44%
300	927	39.06731262	4.21%
325	1014	42.89356133	4.23%
350	1102.5	43.72146745	3.97%
375	1192.5	46.60280484	3.91%
400	1280	48.19769809	3.77%
425	1372.75	49.06416016	3.57%
450	1462.5	48.51118964	3.32%